

60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

16 A

Features

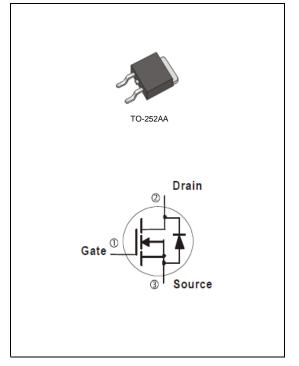
- R_{DS(ON)}, V_{GS}@10V, I_D@8A<50mΩ
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@4A<60m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard



• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	I _D	16		
	T _C =100°C		10	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	64		
Power Dissipation	T _C =25°C	Po	32.6	10/	
	T _C =100°C		16.3	W	
Continuous Drain Current (Note 4)	T _A =25°C	l _D	4.4	^	
	T _A =70°C		3.5	Α	
Power Dissipation	T _A =25°C		2.4	W	
	T _A =70°C	Pb	1.6		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	11	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	R _{θJC}	4.6	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS} V _{GS} =0V, I _D =250uA		60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	1	1.77	2.5	V	
Danier Course On Otata Basistana	R _{DS(on)}	V _{GS} =10V, I _D =8A	-	37	50	mΩ	
Drain-Source On-State Resistance		V _{GS} =4.5V, I _D =4A	-	42	60		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Qg		-	14	-	nC	
Gate-Source Charge	Qgs	V _{DS} =30V, I _D =4A, V _{GS} =10V (Note 1,2)	-	2.9	-		
Gate-Drain Charge	Qgd	VGS=10V (1000 1,2)	-	2.3	-		
Input Capacitance	Ciss	\/ 45\/ \/ 0\/	-	815	-	pF	
Output Capacitance	Coss	V _{DS} =15V, V _{GS} =0V,	-	379	-		
Reverse Transfer Capacitance	Crss	f=1MHZ	-	110	-		
Turn-On Delay Time	td(on)	\/ 00\/ L 44	-	3.9	-		
Turn-On Rise Time	tr	V _{DD} =30V, I _D =1A,	-	13	-	ns	
Turn-Off Delay Time	td(off)	$V_{GS}=10V, R_{G}=3.3\Omega$ (Note 1,2)	-	23	-		
Turn-Off Fall Time	tf	(1000 1,2)	-	6.7	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	1				40		
Diode Forward Current	I _S		-	-	16	A	
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.73	1	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keep initial $T_J=25$ °C.
- 4. The maximum current rating is package limited.
- 5. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =15A, V_{DD} =25V, V_{GS} =10V.
- 7. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

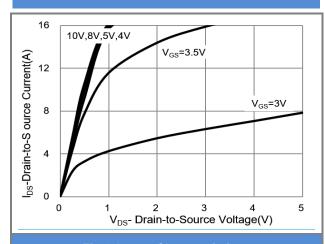


Fig.1 Output Characteristics

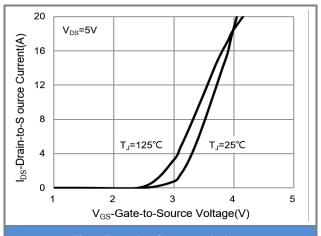


Fig.2 Transfer Characteristics

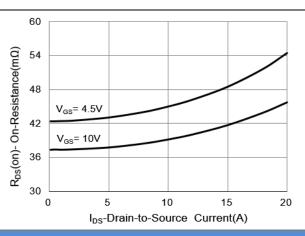


Fig.3 On-Resistance vs. Drain Current

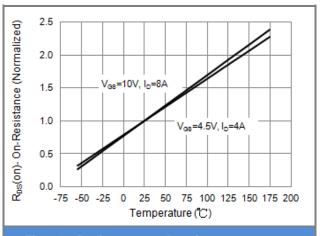


Fig.4 On-Resistance vs. Junction temperature

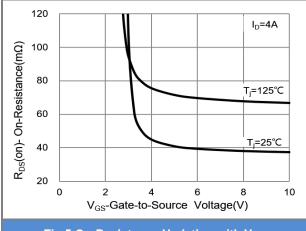


Fig.5 On-Resistance Variation with V_{GS}

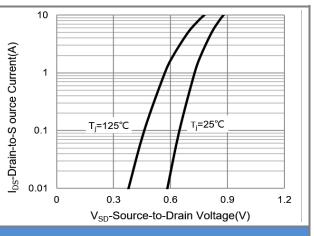


Fig.6 Source-Drain Diode Forward Voltage



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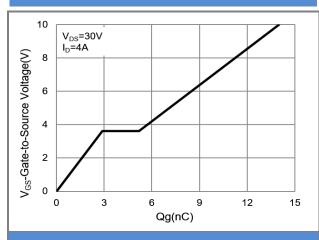


Fig.7 Gate-Charge Characteristics

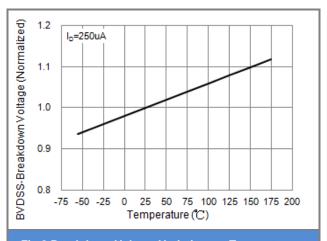


Fig.8 Breakdown Voltage Variation vs. Temperature

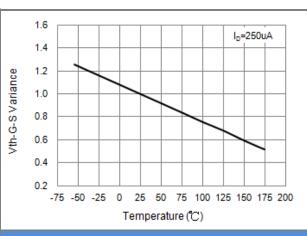


Fig.9 Threshold Voltage Variation with Temperature

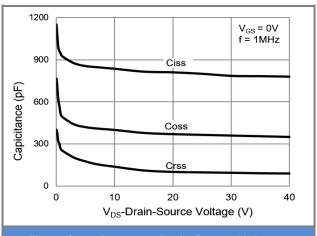
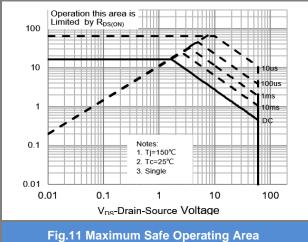


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

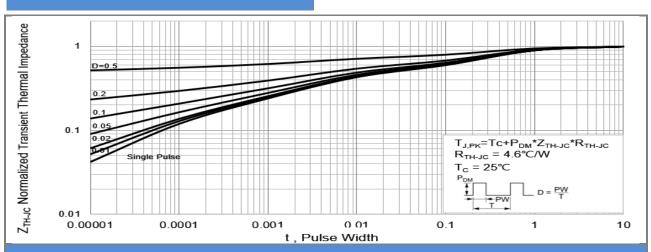


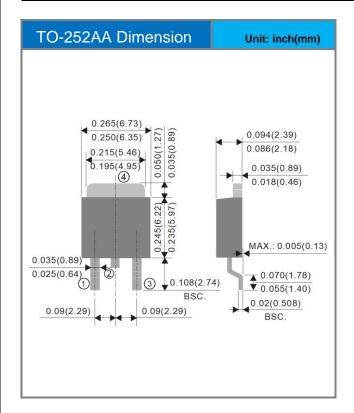
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

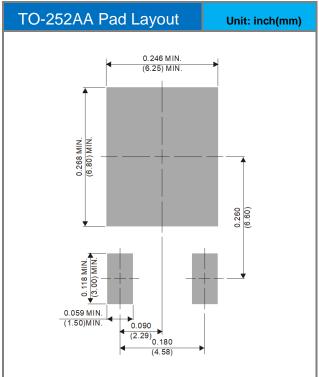


Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJD16N06A-AU	TO-252AA	3,000pcs / 13" reel	D16N06A

Packaging Information & Mounting Pad Layout







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